

DOCKET NO: H0498.70154US00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Charles M. Lieber, et al.  
Serial No: 09/935,776  
Confirmation No: 8935  
Filed: August 22, 2001  
For: DOPED ELONGATED SEMICONDUCTORS, GROWING  
SUCH SEMICONDUCTORS, DEVICES INCLUDING  
SUCH SEMICONDUCTORS AND FABRICATING SUCH  
DEVICES

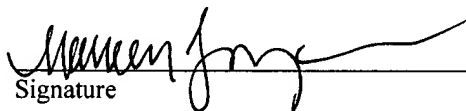
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MAR 10 2004

Examiner: Shouxiang Hu  
Art Unit: 2811

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)

The undersigned hereby certifies that this document is being placed in the United States mail with first-class postage attached, addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the 2 day of March, 2004.

  
Signature

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

STATEMENT FILED PURSUANT TO THE DUTY OF  
DISCLOSURE UNDER 37 CFR §§1.56, 1.97 AND 1.98

Sir:

Pursuant to the duty of disclosure under 37 C.F.R. §§1.56, 1.97 and 1.98, the Applicant requests consideration of this Information Disclosure Statement.

PART I: Compliance with 37 C.F.R. §1.97

This Information Disclosure Statement has been filed more than three months after the filing date of this application and after the mailing date of the first Office Action, but before the mailing date of either a final action under 37 C.F.R. §1.113 or a Notice of Allowance under 37 C.F.R. §1.311, or an action that otherwise closes prosecution in this application.

The fee of \$180.00 as set forth in 37 C.F.R. §1.17(p) is enclosed.

PART II: Information Cited

The Applicant hereby makes of record in the above-identified application the information listed on the attached form PTO-1449 (modified). The order of presentation of the references should not be construed as an indication of the importance of the references.

PART III: Remarks

Documents cited anywhere in the Information Disclosure Statement are enclosed unless otherwise indicated. It is respectfully requested that:

1. The Examiner consider completely the cited information, along with any other information, in reaching a determination concerning the patentability of the present claims;
2. The enclosed form PTO-1449 be signed by the Examiner to evidence that the cited information has been fully considered by the Patent and Trademark Office during the examination of this application;
3. The citations for the information be printed on any patent which issues from this application.

By submitting this Information Disclosure Statement, the Applicant makes no representation that a search has been performed, of the extent of any search performed, or that more relevant information does not exist.

By submitting this Information Disclosure Statement, the Applicant makes no representation that the information cited in the Statement is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b).

By submitting this Information Disclosure Statement, the Applicant makes no representation that the information cited in the Statement is, or is considered to be, in fact, prior art as defined by 35 U.S.C. §102.

Notwithstanding any statements by the Applicant, the Examiner is urged to form his own conclusion regarding the relevance of the cited information.

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An early and favorable action is hereby requested.

Respectfully submitted,

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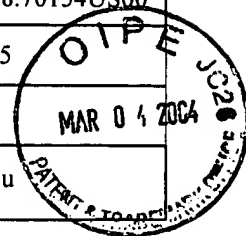
Telephone: (617) 720-3500

Docket No. H0498.70154US00

Date: MARCH 2, 2004

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<b>FORM PTO-1449/A and B (Modified)</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		APPLICATION NO.: 09/935,776	ATTY. DOCKET NO.: H0498.70154US00
		FILING DATE: August 22, 2001	CONFIRMATION NO.: 8935
		APPLICANT: Charles M. Lieber, et al.	
		GROUP ART UNIT: 2811	EXAMINER: Shouxiang Hu
Sheet	1	of	1



#### U.S. PATENT DOCUMENTS

Examiner's Initials	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication or of issue of Cited Document MM-DD-YYYY
		Number	Kind Code		
		2003/0186522	A1	Duan	10-02-2003
		2004/0005723	A1	Empedocles	01-08-2004
		2004/0026684	A1	Empedocles	02-12-2004

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**MAR 10 2004**

#### FOREIGN PATENT DOCUMENTS

Examiner's Initials	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document (not necessary)	Date of Publication of Cited Document MM-DD-YYYY	Translation (Y/N)
		Office/ Country	Number	Kind Code			

#### OTHER ART — NON PATENT LITERATURE DOCUMENTS

Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS) title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, relevant page(s), volume-issue number(s), publisher, city and/or country where published.	Translation (Y/N)
		CHEUNG, C.L., et al., "Diameter Controlled Synthesis of Carbon Nanotubes," <i>J. Phys. Chem B</i> , <b>106</b> , (2002), pp. 2429-2433.	
		DUAN, X., et al., "Nonvolatile Memory and Programmable Logic from Molecule-Gated Nanowires," <i>Nano Letters</i> , <b>2</b> (5), (2002), pp. 487-490.	
		GUDIENSEN, M.S., et al., "Synthetic Control of the Diameter and Length of Single Crystal Semiconductor Nanowires," <i>J. Phys. Chem. B</i> , <b>105</b> , (2001), pp. 4062-4064.	
		HU, J., et al., "Chemistry and Physics in One Dimension: Synthesis and Properties of Nanowires and Nanotubes," <i>Acc. Chem. Res.</i> , <b>32</b> , (1999), pp. 435-445.	
		HU, J., et al., "Controlled growth and electrical properties of heterojunctions of carbon nanotubes and silicon nanowires," <i>Nature</i> , <b>399</b> , (1999), pp. 48-51.	
		HUANG, Y., et al., "Gallium Nitride Nanowire Nanodevices," <i>Nano Letters</i> , <b>2</b> (2), (2002), pp. 101-104.	
		JOSELEVICH, E., et al., "Vectorial Growth of Metallic and Semiconducting Single-Wall Carbon Nanotubes," <i>Nano Letters</i> , <b>2</b> (10), (2002), pp. 1137-1141.	
		RUECKES, T., et al., "Carbon Nanotube-Based Nonvolatile Random Access Memory for Molecular Computing," <i>Science</i> , <b>298</b> , (2000), pp. 94-97.	
		WEI, Q., et al., "Synthesis of Single Crystal Bismuth-Telluride and Lead-Telluride Nanowires for New Thermoelectric Materials," <i>Mat. Res. Soc. Symp. Proc.</i> , <b>581</b> , (2000), pp. 219-223.	

EXAMINER	DATE CONSIDERED
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#EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

\*a copy of this reference is not provided as it was previously cited by or submitted to the office in a prior application, Serial No. \_\_, filed \_\_, and relied upon for an earlier filing date under 35 U.S.C. 120 (continuation, continuation-in-part, and divisional applications).